25C3369

Silicon NPN Epitaxial Planar Type

For high-frequency power amplification

■ Features

- •Intermediate output
- •High power gain PG

■ Absolute Maximum Ratings (Ta=25°C)

Item	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	16	v
Collector-Emitter Voltage	V _{CES}	25	V
Emitter-Base Voltage	V _{EBO}	3	V
Peak Collector Voltage	I _{CP}	0.5	A
Collector Current	$I_{\mathbf{C}}$	0.3	A
Collector Power Dissipation	Pc	1	W
Junction Temperature	Ti	135	°C
Storage Temperature	Tstg	$-55 \sim +135$	°C

■ Electrical Characteristics (Ta=25°C)

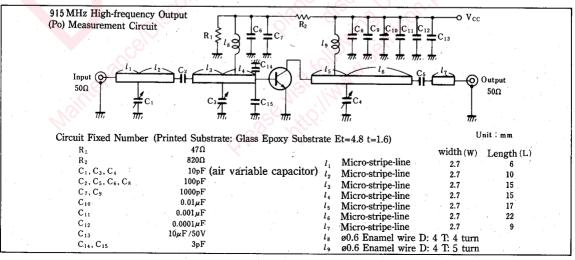
1	0.6	5±0.05 ►1.1	Unit: mm
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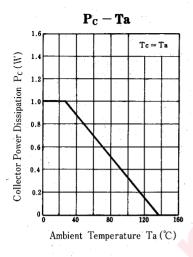
■ Package Dimensions

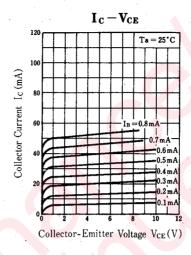
- 1: Collector
 2,4: Emitter(Common)
- 3: Base Cross Pack Package

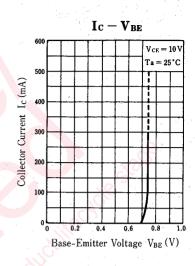
Item	Symbol	Condition	min.	typ.	max.	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 20 \text{ V}, I_E = 0$		×	100	μA
Emitter Cutoff Current	ІЕВО	$V_{EB}=2V$, $I_C=0$		x0°	500	μA
DC Current Gain	h _{FE}	$V_{CE} = 10 \text{ V}, I_{C} = 100 \text{ mA}^{+2}$	20	10	.0	
Collector Output Capacitance	Cob	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	2		6	pF
High-frequency Output	Po*1	$V_{CC} = 8 \text{ V}, P_{in} = 45 \text{ mW}, f = 915 \text{ MHz}$	250	300		mW
Thermal Resistance	ΔV_{BE}	$V_{CB} = 10 \text{ V}, I_E = -100 \text{ mA}, t = 0.8 \text{ s}$.0.	(0.	80	mV

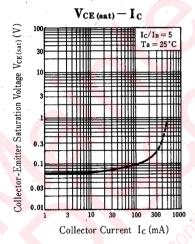
^{*1}Emitter Current *2Pulse Measurement

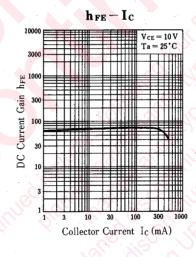


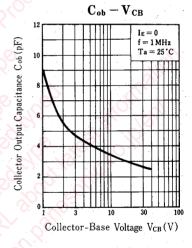


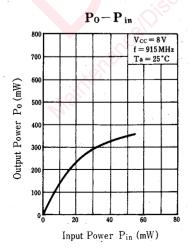












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